



PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/618,824-Conf. #5967 10/18/03
				Filing Date	February 27, 2004
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned LANDAU
Sheet	1	of	1	Attorney Docket Number	M4065.1006/P1006 B

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
ML	AA	US-6,673,648	01/06/2004	Lowrey	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

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NON PATENT LITERATURE DOCUMENTS			
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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

/Matthew Landau/

08/01/2006

2/27/2004

PTO/SB/08A (10-01)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	Not Yet Assigned 10/787123
				Filing Date	February 25, 2004
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned LANDAU
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		Number-Kind Code ² (if known)			
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*	AH	2002/0132417	09/2002	Li	
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*	AT	2003/0047765	03/2003	Campbell	
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MI	AR1	4,316,946	1/1982	Masters, et al.	

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				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned Landau
Sheet	2	of	12	Attorney Docket Number	M4065.1006/P1006-B

ME	AS1	4,320,191	3/1982	Yoshikawa et al.	
*	AT1	4,405,710	9/1983	Balasubramanyam et al.	
*	AU1	4,419,421	12/1983	Wichelhaus, et al.	
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*	AW1	4,671,618	06/1987	Wu et al.	
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Substitute for form 1449A/PTO

(use as many sheets as necessary)

Complete if Known

Attorney Docket Number M4065.1006/P1006-B

Sheet	3	of	12
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				Filing Date	February 25, 2004
				First Named Inventor	Terry L. Gilton
				Art Unit	NTA 2815
				Examiner Name	Not Yet Assigned Landau
Sheet	4	of	12	Attorney Docket Number	M4065.1006/P1006-B

FOREIGN PATENT DOCUMENTS						
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
ML	BA	JP-56126916	10/1981	Akira et al.		
*	BB	WO 97/48032	12/18/1997	Kozicki et al.		
*	BC	WO 99/28914	06/10/1999	Kozicki et al.		
*	BD	WO 00/48196	8/17/00	Arizona Board of Regents		
ML	BE	WO 02/21542-A1	3/14/02	Axon Technologies Corp.		

Examiner Signature	/Matthew Landau/	Date Considered	08/01/2006
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	5	of	12	Attorney Docket Number	M4065.1006/P1006-B

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
ML	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.		
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				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	6	of	12	Attorney Docket Number	M4065.1006/P1006-B

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		Group Art Unit	N/A		
		Examiner Name	Not Yet Assigned		
Sheet	7	of	12	Attorney Docket Number	M4065.1006/P1006-B

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Examiner Signature	/Matthew Landau/	Date Considered	08/01/2006
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